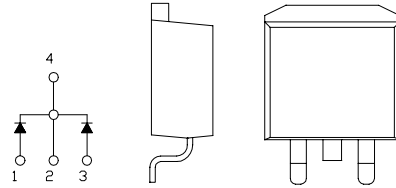


SBD Type : C10T10Q

OUTLINE DRAWING

FEATURES

- *SQUARE-PAK TO-263AB(SMD)
- Packaged in 24mm Tape and Reel
- *Dual Diodes – Cathode Common
- *Low Forward Voltage Drop
- *High Surge Capability
- *T_j=150 °C operation



Maximum Ratings

Approx Net Weight: 1.4g

| Rating | Symbol | C10T10Q | | | Unit |
|-------------------------------------|---------------------|-------------|---|--|------|
| Repetitive Peak Reverse Voltage | V _{RRM} | 100 | | | V |
| Average Rectified Output Current | I _O | 10 | Tc=121°C | 50 Hz Full Sine Wave Resistive Load | A |
| RMS Forward Current | I _{F(RMS)} | 11.1 | | | A |
| Surge Forward Current | I _{FSM} | 120 | 50Hz Full Sine Wave ,1cycle Non-repetitive | | A |
| Operating JunctionTemperature Range | T _{jw} | -40 to +150 | | | °C |
| Storage Temperature Range | T _{stg} | -40 to +150 | | | °C |

Electrical • Thermal Characteristics

| Characteristics | Symbol | Conditions | Min. | Typ. | Max. | Unit |
|----------------------|----------------------|--|------|------|------|-------|
| Peak Reverse Current | I _{RM} | T _j = 25°C, V _{RM} = V _{RRM} per arm | - | - | 1 | mA |
| Peak Forward Voltage | V _{FM} | T _j = 25°C, I _{FM} = 5 A Per arm | - | - | 0.85 | V |
| Thermal Resistance | R _{th(j-c)} | Junction to Case | - | - | 3 | °C /W |

C10T10Q OUTLINE DRAWING (Dimensions in mm)

